

Silicon NPN Power Transistors

2SC2913

DESCRIPTION

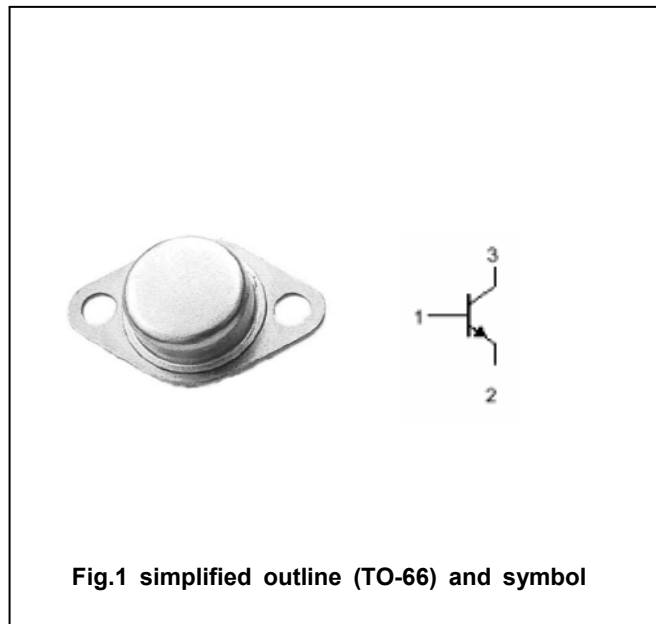
- With TO-66 package
- High breakdown voltage
- Fast switching speed.
- Wide area of safe operation

APPLICATIONS

- For switching regulator applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_B	Base current		3	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA$; $R_{BE}=\infty$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=7A$; $I_B=1.4A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=7A$; $I_B=1.4A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V$; $I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=3A$; $V_{CE}=5V$	12			

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PACKAGE OUTLINE

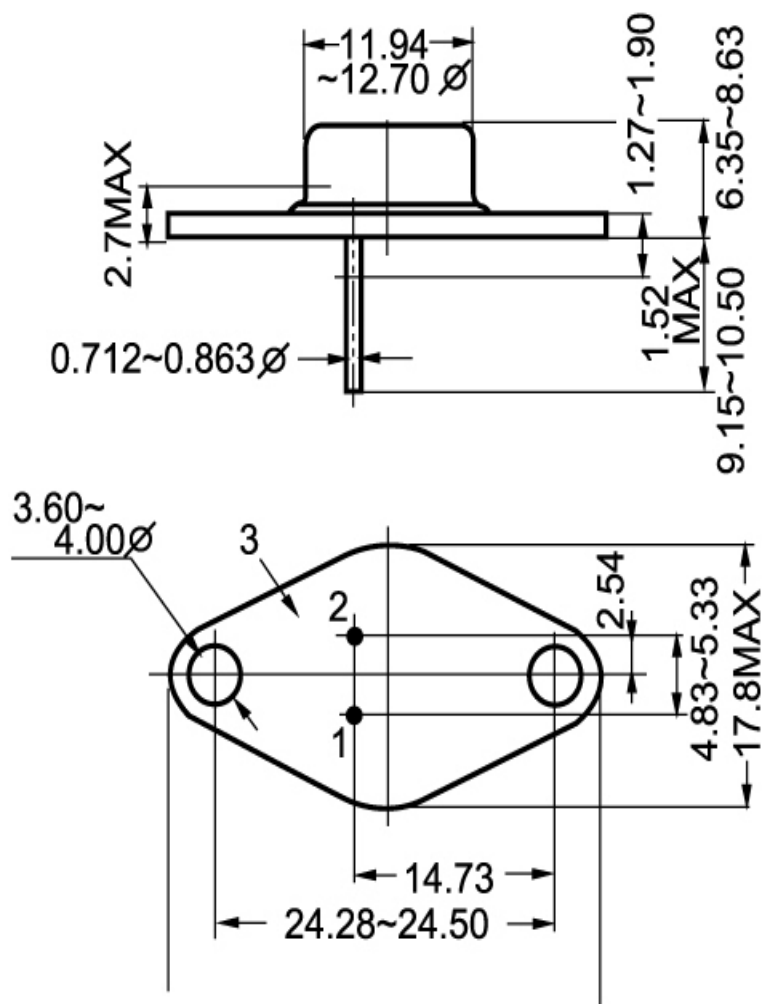


Fig.2 Outline dimensions